

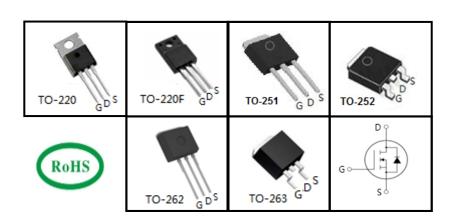
# **600V Super-Junction Power MOSFET**

#### **FEATURES**

- $\bullet \quad \text{Very low FOM R}_{\text{DS(on)}} \times \text{Q}_{\text{g}} \\$
- 100% avalanche tested
- RoHS compliant

#### **APPLICATIONS**

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information						
Device	TPP60R350C	TPA60R350C	TPU60R350C	TPD60R350C	TPC60R350C	TPB60R350C
Package	TO-220	TO-220F	TO-251	TO-252	TO-262	TO-263
Marking	60R350C	60R350C	60R350C	60R350C	60R350C	60R350C

<b>Absolute Maximum Ratings</b> $T_C = 25^{\circ}C$ , unless otherwise noted					
		Value			
Parameter	Symbol	TO-220, TO-251, TO-252 TO-262, TO-263	TO-220F	Unit	
Drain-Source Voltage (V <sub>GS</sub> = 0V)	V <sub>DSS</sub>	600		V	
Continuous Drain Current	I <sub>D</sub>	11		А	
Pulsed Drain Current (note1)	I <sub>DM</sub>	33		А	
Gate-Source Voltage	V <sub>GSS</sub>	±30		V	
Single Pulse Avalanche Energy (note2)	E <sub>AS</sub>	211		mJ	
Avalanche Current (note1)	I <sub>AR</sub>	1.6		А	
Repetitive Avalanche Energy (note1)	E <sub>AR</sub>	0.32		mJ	
Power Dissipation (T <sub>C</sub> = 25°C)	P <sub>D</sub> 78 31.3		W		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55~+150		°C	

Thermal Resistance						
		Value				
Parameter	Symbol	TO-220, TO-251, TO-252 TO-262, TO-263	TO-220F	Unit		
Thermal Resistance, Junction-to-Case	R <sub>thJC</sub>	1.6	4.0	°C/W		
Thermal Resistance, Junction-to-Ambient	R <sub>thJA</sub>	62	80	°C/VV		



### TPP60R350C, TPA60R350C, TPU60R350C, TPD60R350C, TPC60R350C, TPB60R350C

### Wuxi Unigroup Microelectronics Company

<b>Specifications</b> T <sub>J</sub> = 25°C, ur	11033 01110	I I				
Parameter	Symbol	Test Conditions	Value		Unit	
			Min.	Тур.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_{D} = 250\mu A$	600			V
Zero Gate Voltage Drain Current	1	$V_{DS} = 600V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA
Zero Gate Voltage Brain Garrent	I <sub>DSS</sub>	$V_{DS} = 600V, V_{GS} = 0V, T_{J} = 150^{\circ}C$			100	μπ
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30V$			±100	nA
Gate-Source Threshold Voltage	$V_{\rm GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.5		4	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5.5A$		0.30	0.35	Ω
Forward Transconductance (Note3)	$g_{fs}$	$V_{DS} = 10V, I_{D} = 5.5A$		7.8		S
Dynamic				-		
Input Capacitance	C <sub>iss</sub>	$V_{GS} = 0V$ ,		901		pF
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 50V$ ,		50		
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1.0MHz		5.5		
Total Gate Charge	$Q_g$			21		
Gate-Source Charge	$Q_{gs}$	$V_{DD} = 480V, I_{D} = 11A,$ $V_{GS} = 10V$		4.5		nC
Gate-Drain Charge	$Q_{gd}$	65		7		
Turn-on Delay Time	t <sub>d(on)</sub>			41		
Turn-on Rise Time	t <sub>r</sub>	$V_{DD} = 400V, I_{D} = 11A,$		20		
Turn-off Delay Time	t <sub>d(off)</sub>	$R_G = 25\Omega$		123		ns
Turn-off Fall Time	t <sub>f</sub>			6.4		
Drain-Source Body Diode Characteris	stics			•		
Continuous Body Diode Current	I <sub>s</sub>	T 0500			9.2	٨
Pulsed Diode Forward Current	I <sub>SM</sub>	T <sub>C</sub> = 25°C			29	Α
Body Diode Voltage	V <sub>SD</sub>	$T_J = 25^{\circ}C$ , $I_{SD} = 11A$ , $V_{GS} = 0V$		0.9	1.2	V
Reverse Recovery Time	t <sub>rr</sub>			280		ns
Reverse Recovery Charge	Q <sub>rr</sub>	$V_R = 480V, I_F = I_S,$ $di_F/dt = 100A/\mu s$		2.8		μC
Peak Reverse Recovery Current	I <sub>rrm</sub>			17		Α

#### **Notes**

- 1. Repetitive Rating: Pulse Width limited by maximum junction temperature
- 2.  $I_{AS}$  = 1.6A,  $V_{DD}$  = 50V,  $R_{G}$  = 25 $\Omega$ , Starting  $T_{J}$  = 25 $^{\circ}$ C
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 1%

#### **Typical Characteristics** $T_J = 25^{\circ}C$ , unless otherwise noted

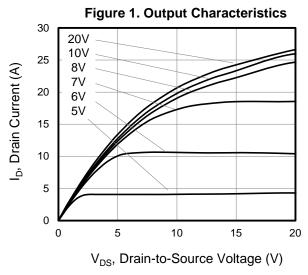


Figure 3. On-Resistance vs. Drain Current

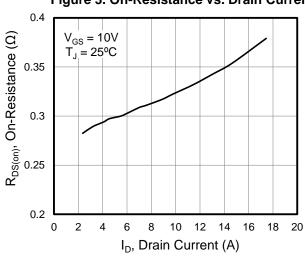
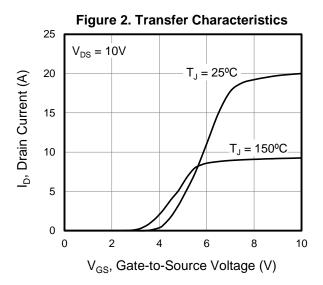
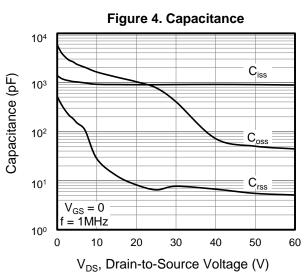


Figure 5. Gate Charge 12 V<sub>GS</sub>, Gate-to-Source Voltage (V) 10  $V_{DD} = 120V$ 8 6  $V_{DD} = 480V$ 4 2 0 0 5 10 15 20 25 Q<sub>q</sub>, Total Gate Charge (nC)





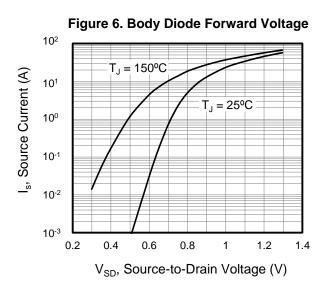


Figure 8. Threshold Voltage vs.

### **Typical Characteristics** $T_J = 25^{\circ}\text{C}$ , unless otherwise noted

Figure 7. On-Resistance vs. **Junction Temperature** 3  $V_{GS} = 10V$ R<sub>DS(on)</sub>, (Normalized) 2.5  $I_{D} = 5.5A$ 2 1.5 1 0.5 0 -100 50 100 150 200 T<sub>J</sub>, Junction Temperature (°C)

Figure 9. Transient Thermal Impedance **TO-220** 10<sup>1</sup> Z<sub>thJC</sub>, Thermal Impedance (K/W) 10<sup>0</sup> 10-1 D = 0.5D = 0.2D = 0.1D = 0.0510-2 D = 0.02D = 0.01Single Pulse 10-3 10-6 10-5 10-2 10<sup>-7</sup> 10-4 10-1 T<sub>p</sub>, Pulse Width (s)

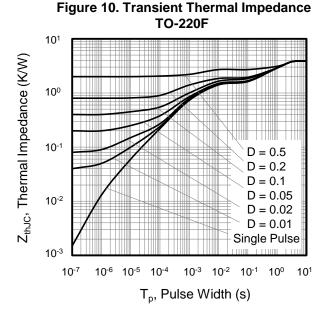




Figure A: Gate Charge Test Circuit and Waveform

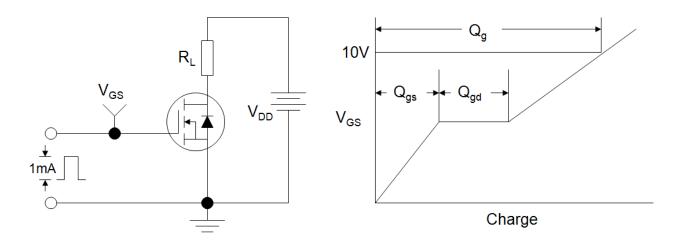


Figure B: Resistive Switching Test Circuit and Waveform

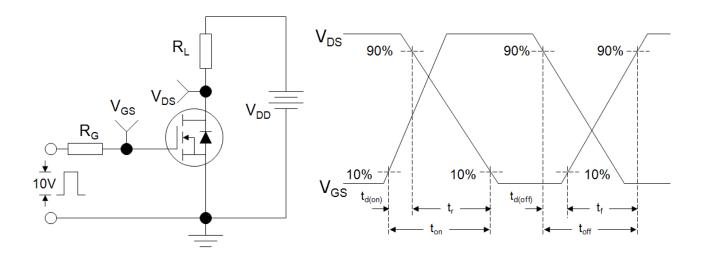
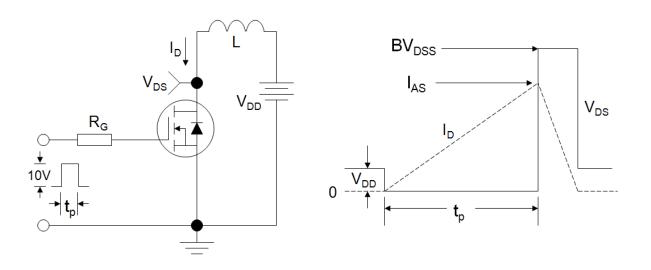
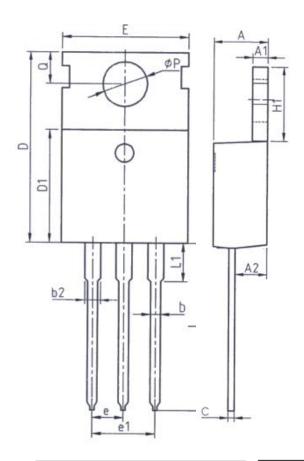
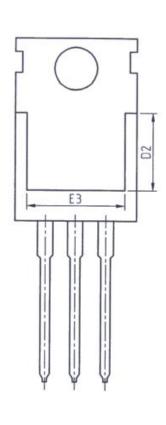


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



**TO-220** 

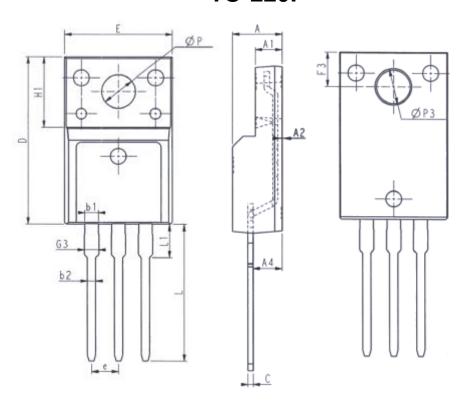




Unit: mm					
Symbol	Min.	Max.			
Α	4. 37	4. 77			
A1	1. 25	1. 45			
A2	2. 20	2. 60			
b	0. 70	0. 95			
b2	1. 17	1. 47			
С	0. 40	0. 65			
D	15. 10	16. 10			
D1	8. 80	9. 40			
D2	5. 50	_			

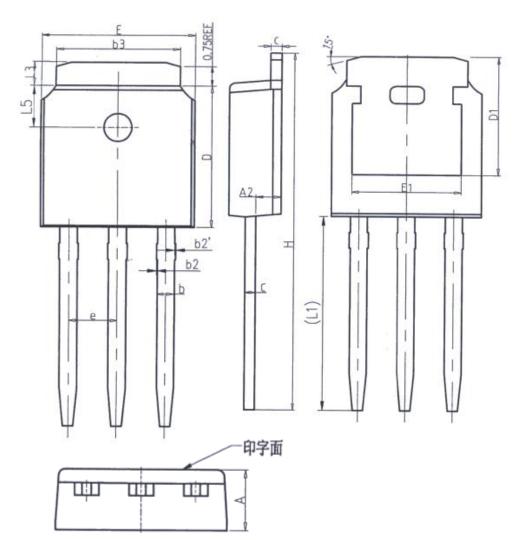
Unit: mm					
Symbol	Min.	Max.			
E	9. 70	10. 30			
E3	7. 00	-			
е	2. 54BSC				
e1	5. 08BSC				
H1	6. 25	6. 85			
L	12. 75	13.80			
L1	-	3. 40			
P	3. 40	3. 80			
Q	2. 60	3. 00			

**TO-220F** 



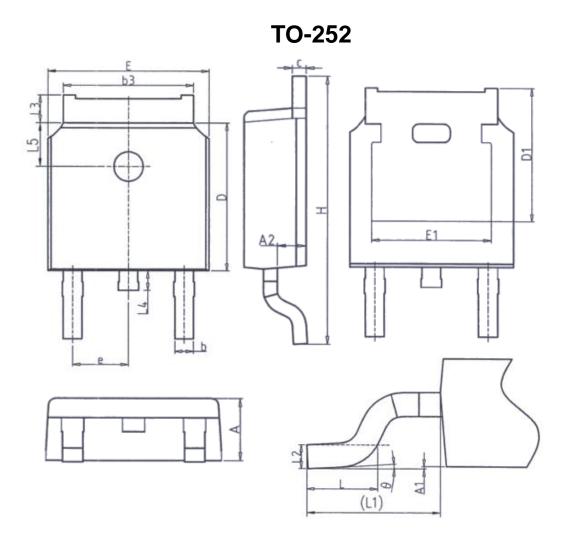
Unit: mm			Unit: mm		
Symbol	Min.	Max.	Symbol	Min.	Max.
E	9.96	10.36	L	12. 68	13. 28
Α	4. 50	4. 90	L1	2. 93	3. 13
A1	2. 34	2. 74	Р	3. 03	3. 38
A2	0. 30	0.60	Р3	3. 15	3. 65
A4	2. 56	2. 96	F3	3. 15	3. 45
С	0.40	0. 65	G3	1. 25	1. 55
D	15. 57	16. 17	b1	1. 18	1. 43
H1	6. 70REF		b2	0. 70	0. 95
е	2. 54BSC				

# **TO-251**



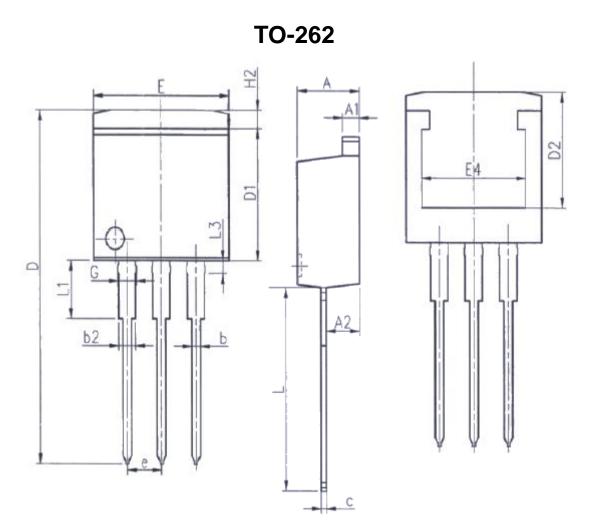
Unit: mm				
Symbol	Min.	Max.		
Α	2. 20	2. 40		
A2	0. 97	1. 17		
b	0. 68	0.90		
b2	0.00	0.10		
b2′	0.00	0.10		
b3	5. 20	5. 50		
С	0. 43	0. 63		
D	5. 98	6. 22		

Unit: mm				
Symbol	Min.	Max.		
D1	5. 30	REF		
E	6. 40	6. 80		
E1	4. 63	-		
е	2. 286BSC			
Н	16. 22	16. 82		
L1	9. 15	9. 65		
L3	0. 88	1. 28		
L5	1. 65	1. 95		



Unit: mm						
Symbol	Min.	Max.				
Α	2. 20	2. 40				
A1	0.00	0. 20				
A2	0. 97	1. 17				
b	0. 68	0. 90				
b3	5. 20	5. 50				
С	0. 43	0. 63				
D	5. 98	6. 22				
D1 5. 30REF						
E	6. 40	6. 80				
E1	4. 63	_				

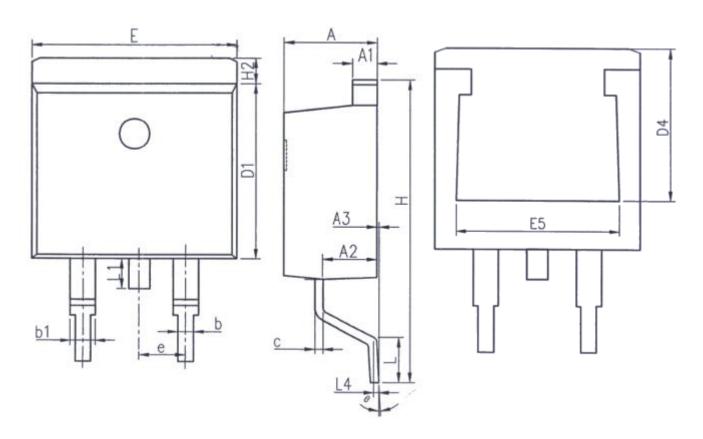
Unit: mm					
Symbol	Min.	Max.			
е	2. 286BSC				
Н	9. 40	10.50			
L	1. 38	1. 75			
L1	2. 90	REF			
L2	0. 51	IBSC			
L3	0.88	1. 28			
L4	- 1.00				
L5	1. 65 1. 95				
θ	0°	8°			



Unit: mm					
Symbol	Min.	Max.			
Α	4. 37	4. 77			
A1	1. 22	1. 42			
A2	2. 47	2. 87			
b	0. 70	0. 97			
b2	1. 17	1. 42			
С	0. 28	0.53			
D	23. 20	24. 02			
D1	8. 38	8. 90			
D2	6. 00	-			

Unit: mm			
Symbol	Min.	Max.	
E	9. 90	10. 39	
E4	7. 30	-	
е	2. 54BSC		
G	1. 25	1.50	
H2	-	1. 31	
L	13. 34	14. 10	
L1	3. 30	4. 06	
L3	0. 95	1. 15	

# **TO-263**



Unit: mm			
Symbol	Min.	Max.	
Α	4. 37	4. 77	
<b>A</b> 1	1. 22	1. 42	
A2	2. 49	2. 89	
A3	0.00	0. 25	
b	0. 70	0.96	
b1	1. 17	1. 47	
С	0. 30	0.53	
D1	8. 50	8. 90	
D4	6. 60	-	

Unit: mm			
Symbol	Min.	Max.	
E	9.86	10.36	
E5	7. 06	-	
е	2. 54BSC		
Н	14. 70	15. 50	
H2	1. 07	1. 47	
L	2.00	2. 60	
L1	1. 40	1. 70	
L4	0. 25BSC		
θ	0°	9°	



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